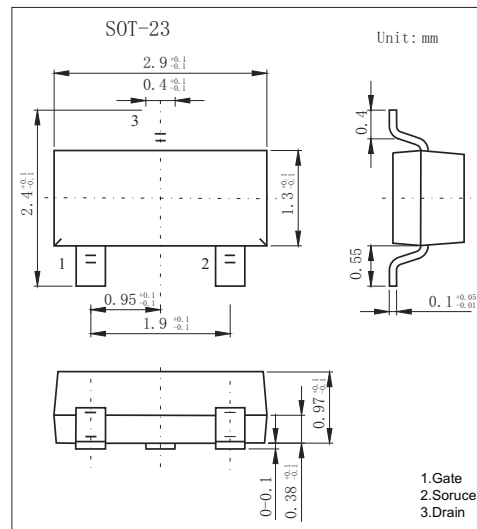


627 3ODVWLF (QFDSVXODWH 026)(76

V ; ^ } & @ Ø V Á Ú [ , ^ ; Á T U Ò Ø V Á  
 Þ É Ò @ æ } ^ Á H E É X Á Ç Ö È Ú D Á T U Ò Ø V Á  
 0 ( & + \$ 1 , & \$ / ' \$ 7 \$  
 & D V H V W \ O H 6 2 7 P R O G H G S O D V W L F  
 O R X Q W L Q J S R V L W L R Q D Q \



0 \$ ; , 0 8 0 5 \$ 7 , 1 \* 6 \$ 1 ' & + \$ 5 \$ & 7 ( 5 , 6 7 , & 6

# & \$ P E L H Q W 7 H P S H U D W X U H X Q O H V V R W K H U Z L V H Q R W H G

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V <sub>DS</sub>	30	V
Gate-Source Voltage	V <sub>GS</sub>	±20	
Continuous Drain Current (T <sub>J</sub> = 150°C) *2 Ta = 25°C	I <sub>D</sub>		A
Ta=70°C	P <sub>D</sub>	1.25	W
		0.80	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C
Maximum Junction-to-Ambient <sup>b</sup>	R <sub>thJA</sub>	100	°C/W
Maximum Junction-to-Ambient <sup>c</sup>		166	

\*1 Pulse width limited by maximum junction temperature.

\*2 Surface Mounted on FR4 Board, t ≤ 5 sec.

\*3 Surface Mounted on FR4 Board.

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{ A}$	30			
Gate-Threshold Voltage	$V_{GS(th)}$					